

In the Specification:

Please amend the specification to read as follows:

Page 7, paragraph 1:

B₁ As etching proceeds, the DC voltage across the plasma system 104 changes ~~104~~. This DC shift is caused by both a change in the sheath voltage and by change in the thickness of the oxide layer that is being etched. Refer to Figure 2. a mask 200 covers an oxide layer 202 to control etching of the oxide. Beneath the oxide layer is a nitride layer 204, followed by a substrate 206. As the oxide layer 202 becomes thinner, the charge ~~208 deposited on the surface of the etched oxide 202~~ attracts charge 210 from the far side of the nitride 204 to form a capacitance. As the oxide layer 202 thins, this capacitance changes. The change in the system is reflected in the voltage across resistors within the matching circuit that are connected between the high node of the plasma chamber and ground.